

PNP High Voltage Amplifier

This device is designed for high voltage driver applications. Sourced from Process 76.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	300	V	
V _{CBO}	Collector-Base Voltage	300	V	
V _{EBO}	Emitter-Base Voltage	5.0	V	
lc	Collector Current - Continuous	500	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	۵°	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах			Units
		MPSA92	*MMBTA92	**PZTA92	
Pp	Total Device Dissipation	625	350	1,000	mW
	Derate above 25°C	5.0	2.8	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

** Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

PNP High Voltage Amplifier (c

continued	

Symbol Parameter	Test Conditions	Min	Мах	Units
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OFF CHARACTERISTICS

V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	300		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	300		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 100 \ \mu A, \ I_{C} = 0$	5.0		V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 200 \text{ V}, I_E = 0$		0.25	μA
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 3.0 \text{ V}, \text{ I}_{C} = 0$		0.1	μΑ

ON CHARACTERISTICS*

h _{FE}	DC Current Gain	I _C = 1.0 mA, V _{CE} = 10 V	25		
		$I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$	40		
		$I_{C} = 30 \text{ mA}, V_{CE} = 10 \text{ V}$	25		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 20$ mA, $I_{\rm B} = 2.0$ mA		0.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 20$ mA, $I_{\rm B} = 2.0$ mA		0.9	V

SMALL SIGNAL CHARACTERISTICS

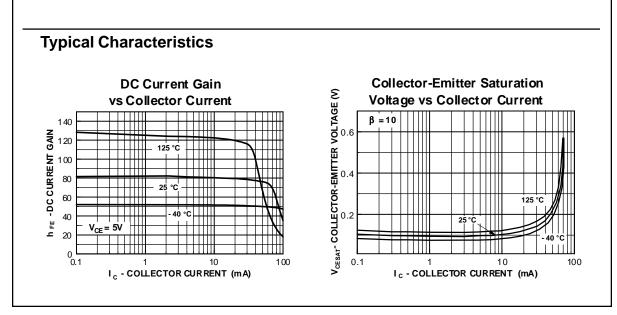
f _T	Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100 MHz	50		MHz
C _{cb}	Collector-Base Capacitance	$V_{CB} = 20 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		6.0	pF

*Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%

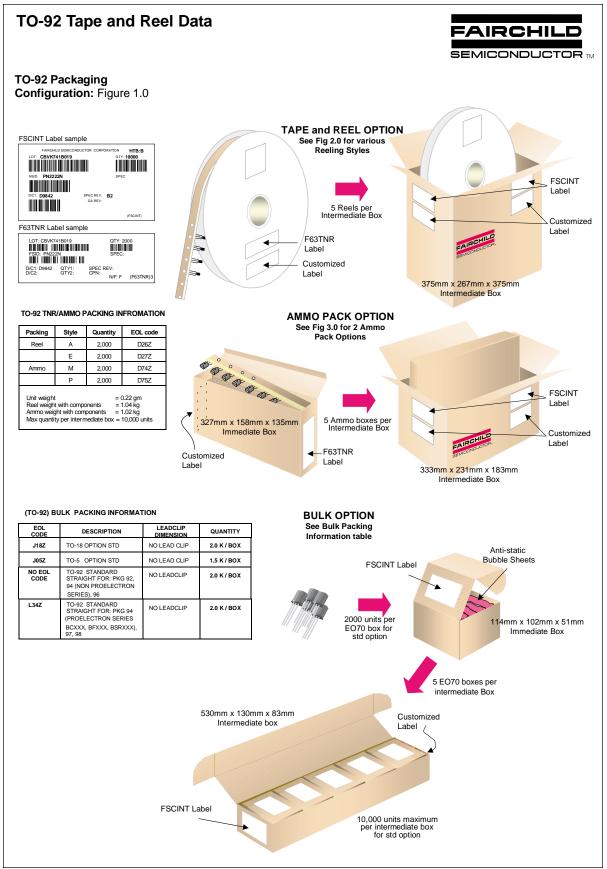
 $\textbf{NOTE:} \ \textbf{All voltages} \ (V) \ \textbf{and} \ \textbf{currents} \ (A) \ \textbf{are negative polarity for PNP transistors}.$

Spice Model

PNP (Is=218.9f Xti=3 Eg=1.11 Vaf=100 Bf=99 Ne=1.307 Is=218.9f Ikf=.2016 Xtb=1.5 Br=24.67 Nc=2 Isc=0 Ikr=0 Rc=7 Cjc=19.88p Mjc=.4876 Vjc=.75 Fc=.5 Cje=81.49p Mje=.3493 Vje=.75 Tr=516.9p Tf=1.395n Itf=1.5 Vtf=22 Xtf=270 Rb=10)

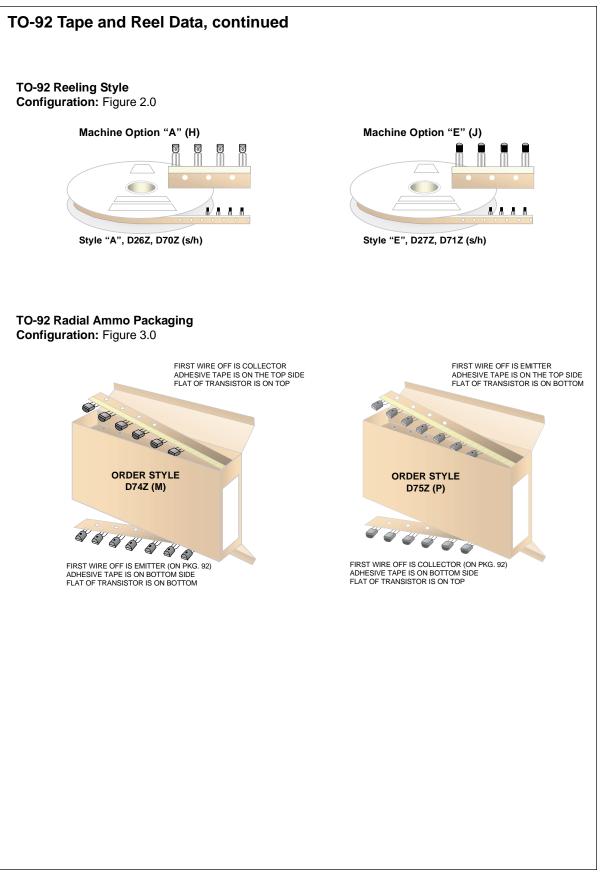


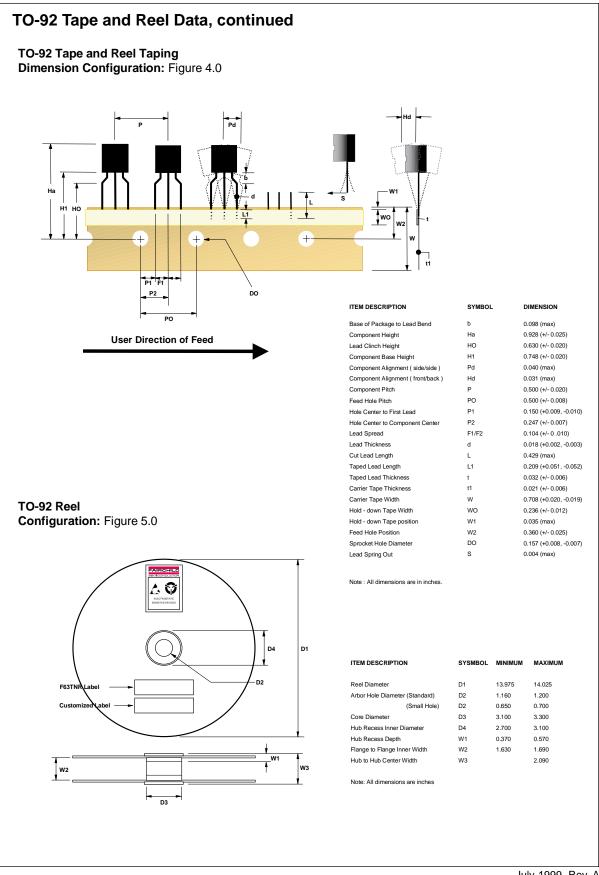
MPSA92 / MMBTA92 / PZTA92 **PNP High Voltage Amplifier** (continued) Typical Characteristics (continued) **Base-Emitter Saturation** Base-Emitter ON Voltage vs Voltage vs Collector Current **Collector Current voltage (v)** 40 °C 40 °C - **BASE-EMITTER** 0.7 ; °C 25 25 0.6 Ħ 125 °C 125 °C 0.5 V_{CE}= 5V β = 10 0.4 . 0.4 Ly and 0.3 1 10 100 1 10 100 I c - COLLECTOR CURRENT (mA) I_c - COLLECTOR CURRENT (mA) **Junction Capacitance Collector-Cutoff Current** vs Reverse Bias Voltage vs Ambient Temperature 10 100 I_{CB0} - COLLECTOR CURRENT (nA) JUNCTION CAPACITANCE (pF) f = 1.0 MHz V_{CB}= 150 V Cib 10 1 0.1 0.1 └ 0.1 1 V_R - REVERSE VOLTAGE (V) 100 25 50 75 100 125 150 T_A - AMBIENT TEMPERATURE (°C) **Gain Bandwidth Product Power Dissipation vs** vs Collector Current **Ambient Temperature** f_{T} - GAIN BANDWIDTH PRODUCT (MHz) 100 V_{CE} = 50V **b** - 0.75 0.5 0.25 - 0.25 80 SOT-223 TO-92 V_{CE} = 15V 60 SOT-23 40 20 0 • 0 50 75 100 TEMPERATURE (°C) 25 10 20 Ic - COLLECTOR CURRENT (mA) 125 150 50 100



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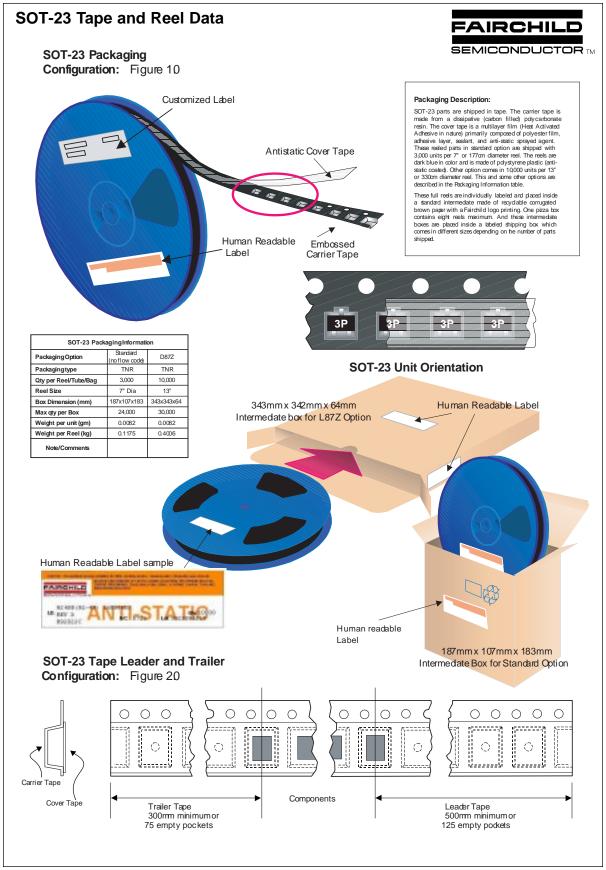
March 2001, Rev. B1





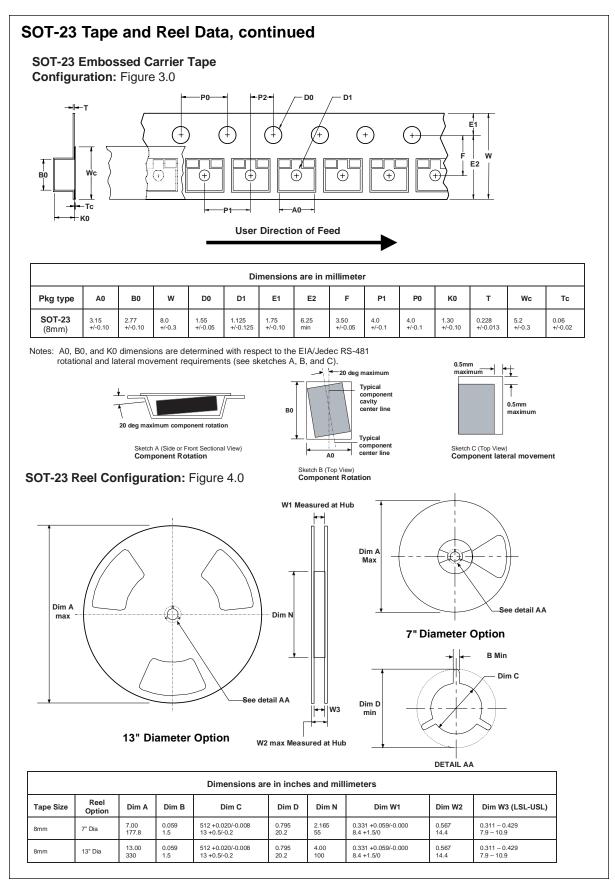
July 1999, Rev. A



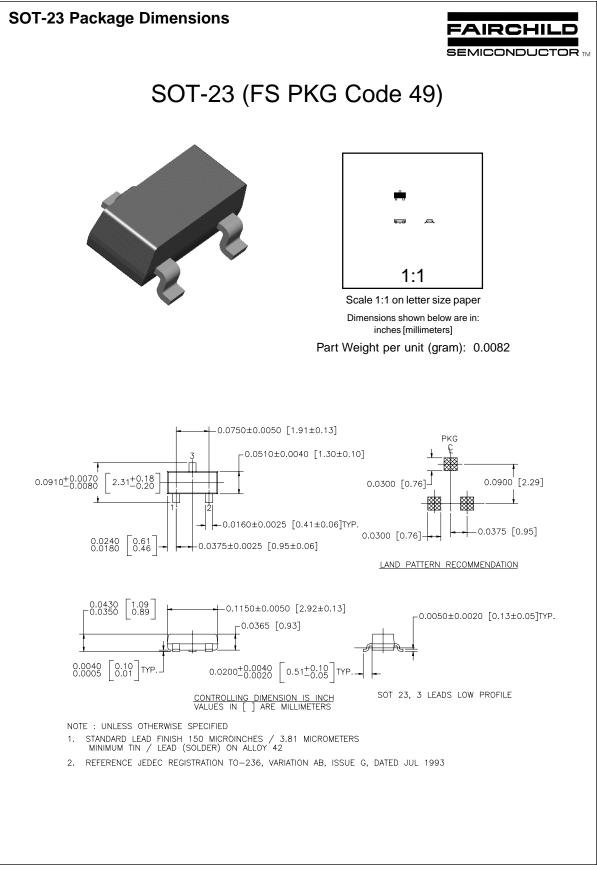


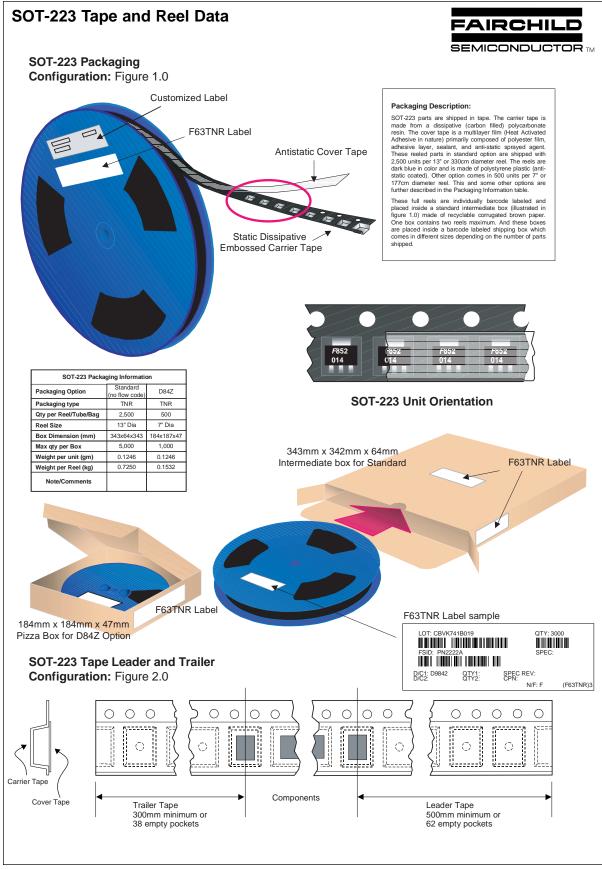
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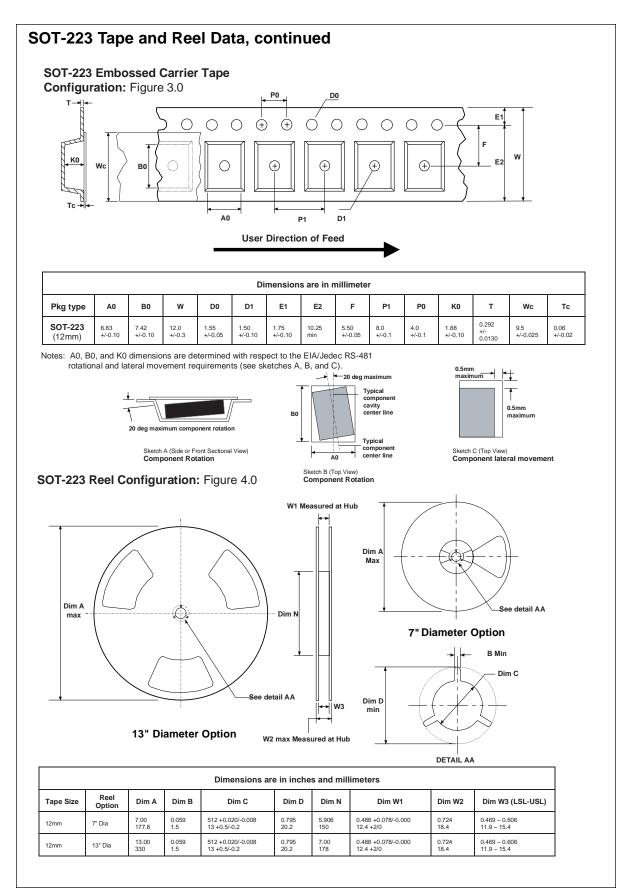
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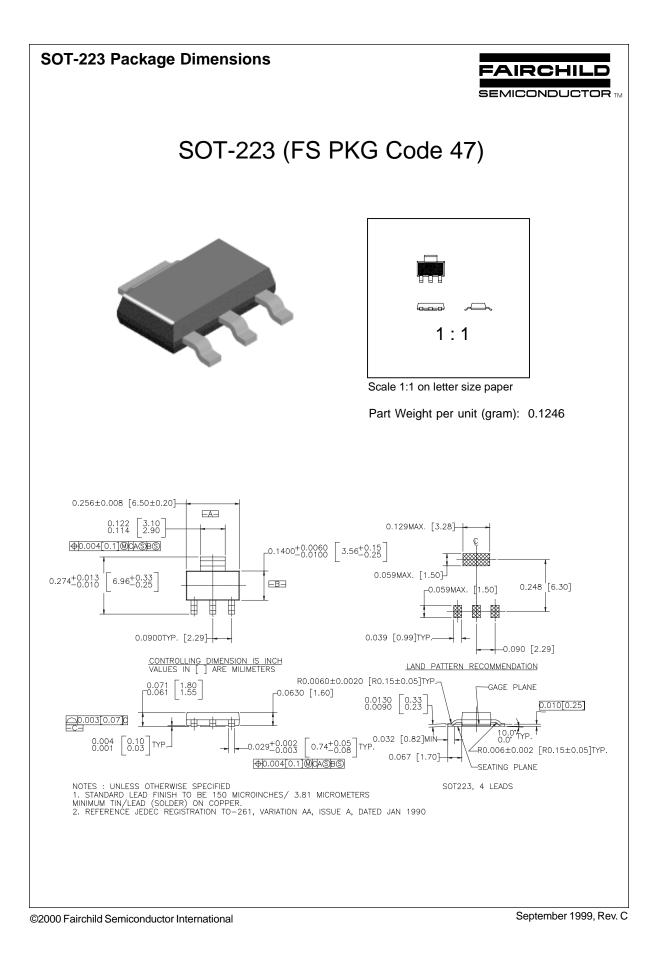




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